

TPS56x210 采用 8 引脚 SOT-23 封装的 4.5V 至 17V 输入、2A/3A 同步降压稳压器

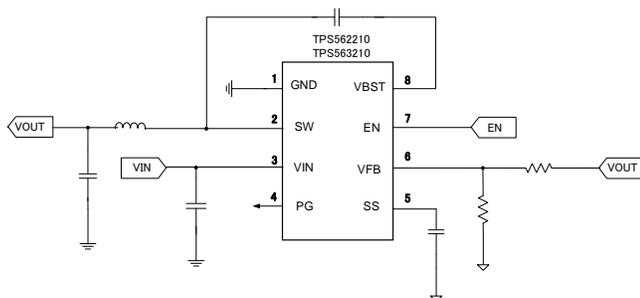
1 特性

- TPS562210: 2A 转换器, 具有 133mΩ 和 80mΩ 集成场效应晶体管 (FET)
- TPS563210: 3A 转换器, 具有 68mΩ 和 39mΩ 集成 FET
- D-CAP2™ 针对快速瞬态响应的模式控制
- 高级 Eco-mode™ 脉冲跳跃
- 输入电压范围: 4.5V 至 17V
- 输出电压范围: 0.76V 至 7V
- 650kHz 开关频率
- 低关断电流 (低于 10μA)
- 1% 反馈电压精度 (25°C)
- 从预偏置输出电压中启动
- 逐周期过流限制
- 断续模式欠压保护
- 非锁存过压保护 (OVP), 欠压闭锁 (UVLO) 和热关断 (TSD) 保护
- 可调软启动
- 电源正常输出

2 应用

- 数字电视电源
- 高清 Blu-ray Disc™ 播放器
- 网络家庭终端设备
- 数字机顶盒 (STB)

4 简化电路原理图



3 说明

TPS562210 和 TPS563210 是采用 8 引脚小外形尺寸晶体管 (SOT)-23 封装的简单易用型 2A/3A 同步降压转换器。

此器件被优化为使用尽可能少的外部组件即可运行, 并且可以实现低待机电流。

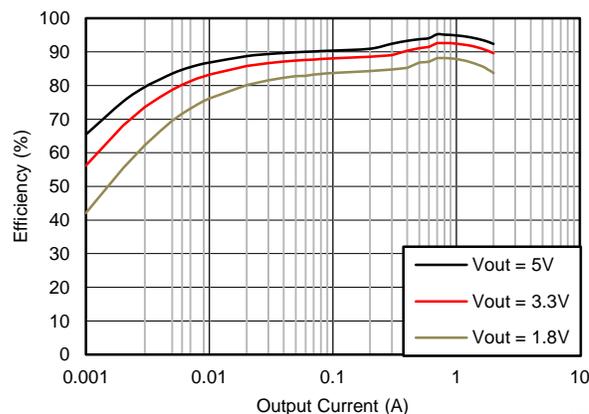
这些开关模式电源 (SMPS) 器件采用 D-CAP2™ 模式控制, 从而提供快速瞬态响应, 并且在无需外部补偿组件的情况下支持诸如高分子聚合物等低等效串联电阻 (ESR) 输出电容器以及超低 ESR 陶瓷电容器。

该器件可在高级 Eco-mode™ 下运行, 从而能在轻载运行期间保持高效率。TPS562210 和 TPS563210 采用 8 引脚 1.6mm × 2.9mm SOT (DDF) 封装, 额定环境温度范围为 -40°C 至 85°C。

器件信息(1)

订货编号	封装	封装尺寸 (标称值)
TPS562210DDFT	DDF(8)	1.60mm x 2.90mm
TPS562210DDFR		
TPS563210DDFT		
TPS563210DDFR		

(1) 要了解所有可用封装, 请见数据表末尾的可订购产品附录。



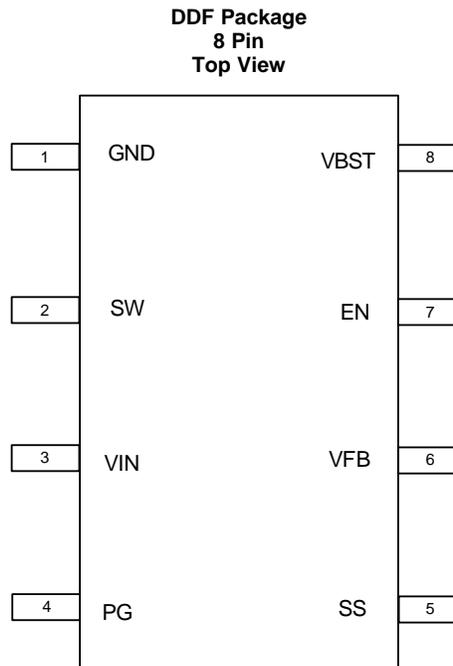
目录

1 特性	1	8.2 Functional Block Diagram	11
2 应用	1	8.3 Feature Description	11
3 说明	1	8.4 Device Functional Modes	13
4 简化电路原理图	1	9 Application and Implementation	14
5 修订历史记录	2	9.1 Application Information	14
6 Pin Configuration and Functions	3	9.2 Typical Application	14
7 Specifications	4	10 Power Supply Recommendations	23
7.1 Absolute Maximum Ratings	4	11 Layout	24
7.2 ESD Ratings	4	11.1 Layout Guidelines	24
7.3 Recommended Operating Conditions	4	11.2 Layout Example	24
7.4 Thermal Information	4	12 器件和文档支持	25
7.5 Electrical Characteristics	5	12.1 相关链接	25
7.6 Timing Requirements	6	12.2 社区资源	25
7.7 Typical Characteristics: TPS562210	7	12.3 商标	25
7.8 Typical Characteristics: TPS563210	9	12.4 静电放电警告	25
8 Detailed Description	11	12.5 Glossary	25
8.1 Overview	11	13 机械、封装和可订购信息	26

5 修订历史记录

Changes from Original (February 2015) to Revision A	Page
• Changed the <i>Thermal Information</i> values for TPS563210	4
• Changed the V_{FBTH} values in the <i>Electrical Characteristics</i> From: MIN = 757, MAX = 773 To: MIN = 758, MAX = 772	5
• Changed I_{VFB} spec UNIT from "mA" to "µA"	5
• Changed $T_{HiccupOn}$ in the <i>Electrical Characteristics</i> From TYP = 1 ms To: TYP = 1 cycle	5
• Changed $T_{HiccupOff}$ in the <i>Electrical Characteristics</i> From TYP = 1.7 ms To: TYP = 7 cycles	5
• Changed $V_{out} = 5V$ to $V_{out} = 1.8V$ in Figure 6	7
• Changed column heading C8 + C9 (µF) To: C6 + C7 + C8 (µF) in Table 2	15
• Changed column heading C8 + C9 (µF) To: C6 + C7 + C8 (µF) in Table 4	19

6 Pin Configuration and Functions



Pin Functions

PIN		DESCRIPTION
NAME	NO.	
GND	1	Ground pin Source terminal of low-side power NFET as well as the ground terminal for controller circuit. Connect sensitive VFB to this GND at a single point.
SW	2	Switch node connection between high-side NFET and low-side NFET.
VIN	3	Input voltage supply pin. The drain terminal of high-side power NFET.
PG	4	Power good open drain output
SS	5	Soft-start control. An external capacitor should be connected to GND.
VFB	6	Converter feedback input. Connect to output voltage with feedback resistor divider.
EN	7	Enable input control. Active high and must be pulled up to enable the device.
VBST	8	Supply input for the high-side NFET gate drive circuit. Connect 0.1 μ F capacitor between VBST and SW pins.

7 Specifications

7.1 Absolute Maximum Ratings

 $T_J = -40^{\circ}\text{C}$ to 150°C (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
Input voltage range	VIN, EN	-0.3	19	V
	VBST	-0.3	25	V
	VBST (10 ns transient)	-0.3	27.5	V
	VBST (vs SW)	-0.3	6.5	V
	VFB, PG	-0.3	6.5	V
	SS	-0.3	5.5	V
	SW	-2	19	V
	SW (10 ns transient)	-3.5	21	V
Operating junction temperature, T_J		-40	150	$^{\circ}\text{C}$
Storage temperature, T_{stg}		-55	150	$^{\circ}\text{C}$

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	± 2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	± 500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

 $T_J = -40^{\circ}\text{C}$ to 150°C (unless otherwise noted)

		MIN	MAX	UNIT	
V_{IN}	Supply input voltage range	4.5	17	V	
V_I	Input voltage range	VBST	-0.1	23	V
		VBST (10 ns transient)	-0.1	26	V
		VBST(vs SW)	-0.1	6	V
		EN	-0.1	17	V
		VFB, pg	-0.1	5.5	V
		SS	-0.1	5	V
		SW	-1.8	17	V
		SW (10 ns transient)	-3.5	20	V
T_A	Operating free-air temperature	-40	85	$^{\circ}\text{C}$	

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS562210	TPS563210	UNIT
		DDF (8 PINS)		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	106.1	87.0	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	49.1	41.6	$^{\circ}\text{C}/\text{W}$
$R_{\theta JB}$	Junction-to-board thermal resistance	10.9	14.6	$^{\circ}\text{C}/\text{W}$
Ψ_{JT}	Junction-to-top characterization parameter	8.6	4.7	$^{\circ}\text{C}/\text{W}$
Ψ_{JB}	Junction-to-board characterization parameter	10.8	14.6	$^{\circ}\text{C}/\text{W}$

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

7.5 Electrical Characteristics

over operating free-air temperature range, $V_{IN} = 12\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY CURRENT						
I_{VIN}	Operating – non-switching supply current	V_{IN} current, $T_A = 25^\circ\text{C}$, $EN = 5\text{ V}$, $V_{FB} = 0.8\text{ V}$		190	290	μA
I_{VNSDN}	Shutdown supply current	V_{IN} current, $T_A = 25^\circ\text{C}$, $EN = 0\text{ V}$		3.0	10	μA
LOGIC THRESHOLD						
V_{ENH}	EN high-level input voltage	EN	1.6			V
V_{ENL}	EN low-level input voltage	EN			0.6	V
R_{EN}	EN pin resistance to GND	$V_{EN} = 12\text{ V}$	225	450	900	k Ω
V_{FB} VOLTAGE AND DISCHARGE RESISTANCE						
V_{FBTH}	V_{FB} threshold voltage TPS562210	$T_A = 25^\circ\text{C}$, $V_O = 1.05\text{ V}$, $I_O = 10\text{ mA}$, Eco-mode™ operation		772		mV
		$T_A = 25^\circ\text{C}$, $V_O = 1.05\text{ V}$	758	765	772	mV
	V_{FB} threshold voltage TPS562210 and TPS563210	$T_A = 0^\circ\text{C}$ to 85°C , $V_O = 1.05\text{ V}^{(1)}$	753		777	
		$T_A = -40^\circ\text{C}$ to 85°C , $V_O = 1.05\text{ V}^{(1)}$	751		779	
I_{VFB}	V_{FB} input current	$V_{FB} = 0.8\text{ V}$, $T_A = 25^\circ\text{C}$		0	± 0.1	μA
MOSFET						
$R_{DS(on)h}$	High side switch resistance	$T_A = 25^\circ\text{C}$, $V_{BST} - SW = 5.5\text{ V}$, TPS562210		133		m Ω
		$T_A = 25^\circ\text{C}$, $V_{BST} - SW = 5.5\text{ V}$, TPS563210		68		
$R_{DS(on)l}$	Low side switch resistance	$T_A = 25^\circ\text{C}$, TPS562210		80		m Ω
		$T_A = 25^\circ\text{C}$, TPS563210		39		
CURRENT LIMIT						
I_{oc1}	Current limit ⁽¹⁾	DC current, $V_{OUT} = 1.05\text{ V}$, $L1 = 2.2\text{ }\mu\text{H}$, TPS562210	2.5	3.2	4.3	A
		DC current, $V_{OUT} = 1.05\text{ V}$, $L1 = 1.5\text{ }\mu\text{H}$, TPS563210	3.5	4.2	5.3	
THERMAL SHUTDOWN						
T_{SDN}	Thermal shutdown threshold ⁽¹⁾	Shutdown temperature		155		$^\circ\text{C}$
		Hysteresis		35		
SOFT START						
I_{ss}	SS charge current	$V_{SS} = 0.5\text{ V}$	4.2	6	7.8	μs
	SS discharge current	$V_{SS} = 0.5\text{ V}$, $EN = L$	0.75	1.3		mA
POWER GOOD						
V_{THPG}	PG threshold	VFB rising (Good)	85%	90%	95%	
		VFB falling (Fault)		85%		
IPG	PG sink current	PG = 0.5 V	0.5	1		mA
OUTPUT UNDERVOLTAGE AND OVERVOLTAGE PROTECTION						
V_{OVP}	Output OVP threshold	OVP Detect		125% \times V_{fbth}		
V_{UVP}	Output UVP threshold	Hiccup detect		65% \times V_{fbth}		
$T_{HiccupOn}$	Hiccup Power On Time	Relative to soft start time		1		cycle
$T_{HiccupOff}$	Hiccup Power Off Time	Relative to soft start time		7		cycles
UVLO						
UVLO	UVLO threshold	Wake up V_{IN} voltage	3.45	3.75	4.05	V
		Hysteresis V_{IN} voltage	0.13	0.32	0.55	

(1) Not production tested.

TPS562210, TPS563210

ZHCSE05A – FEBRUARY 2015 – REVISED AUGUST 2015

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7.6 Timing Requirements

			MIN	TYP	MAX	UNIT
ON-TIME TIMER CONTROL						
t_{ON}	On time	$V_{IN} = 12\text{ V}, V_O = 1.05\text{ V}$		150		ns
$t_{OFF(MIN)}$	Minimum off time	$T_A = 25^\circ\text{C}, V_{FB} = 0.5\text{ V}$		260	310	ns

7.7 Typical Characteristics: TPS562210

$V_{IN} = 12\text{ V}$ (unless otherwise noted)

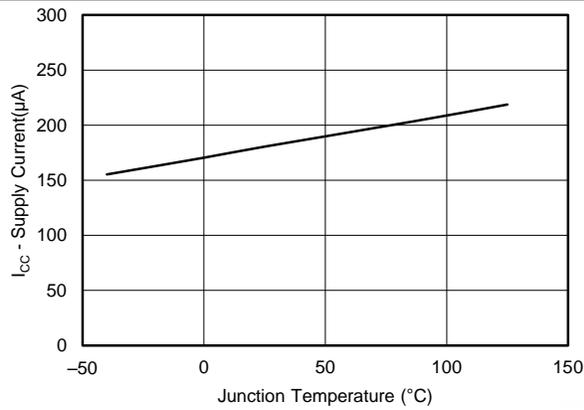


Figure 1. Supply Current vs Junction Temperature

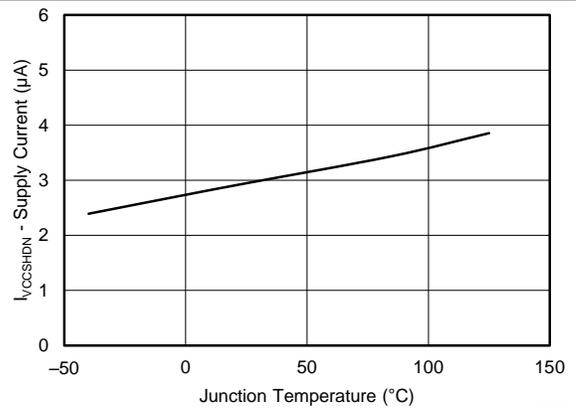


Figure 2. VIN Shutdown Current vs Junction Temperature

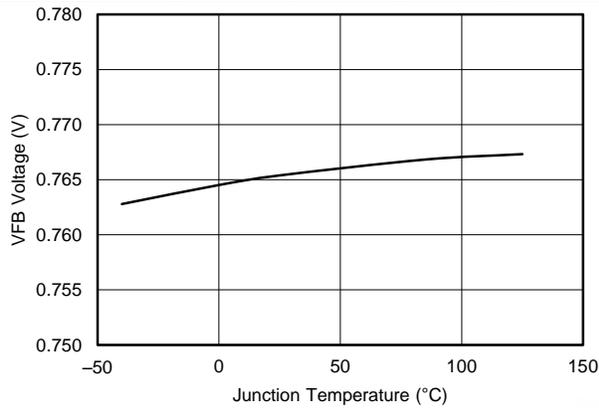


Figure 3. VFB Voltage vs Junction Temperature

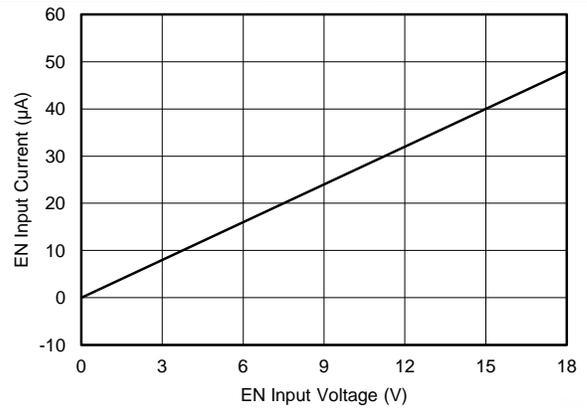


Figure 4. EN Current vs EN Voltage

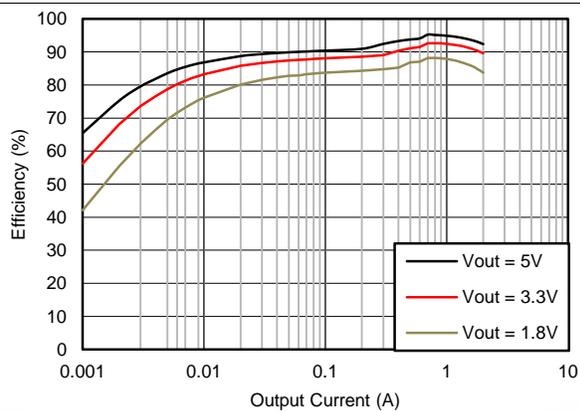


Figure 5. Efficiency vs Output Current

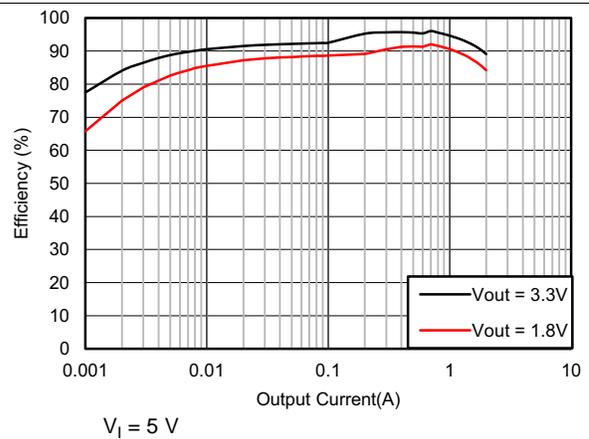
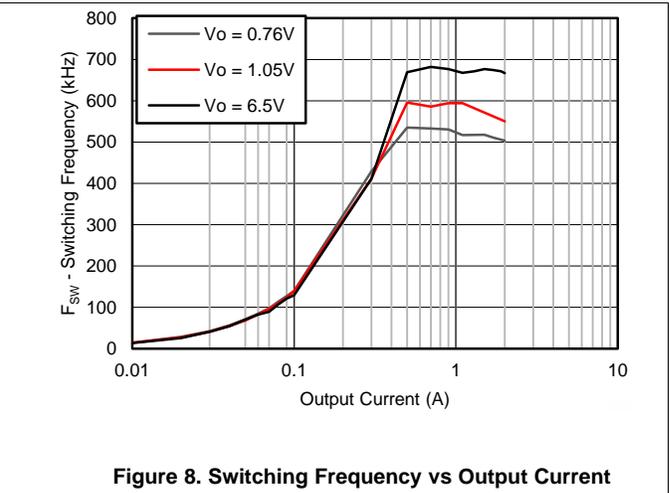
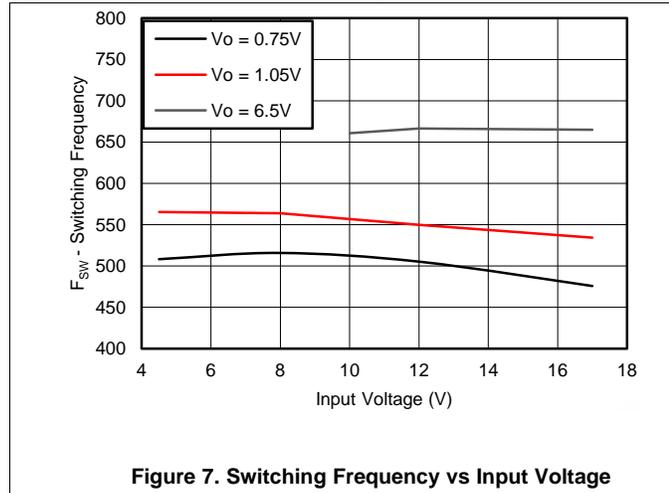


Figure 6. Efficiency vs Output Current

Typical Characteristics: TPS562210 (continued)

$V_{IN} = 12\text{ V}$ (unless otherwise noted)



7.8 Typical Characteristics: TPS563210

$V_{IN} = 12V$ (unless otherwise noted)

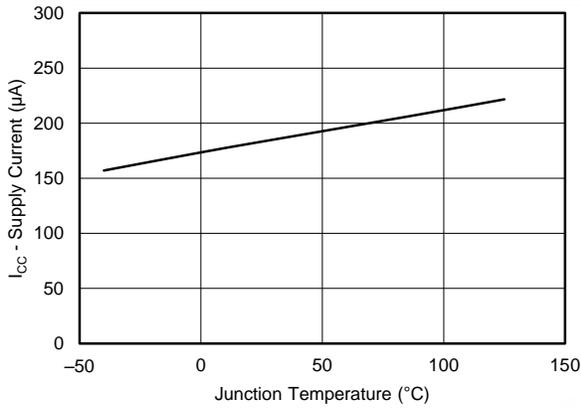


Figure 9. Supply Current vs Junction Temperature

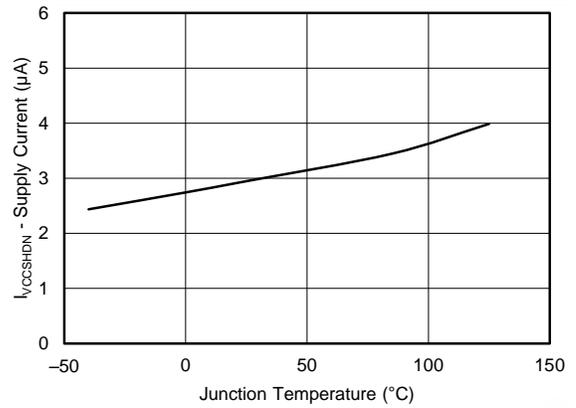


Figure 10. VIN Shutdown Current vs Junction Temperature

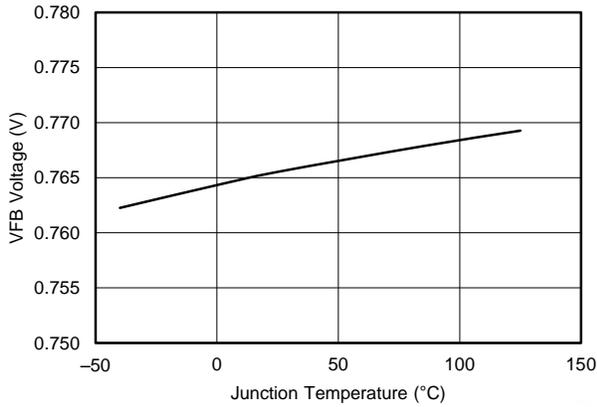


Figure 11. VFB Voltage vs Junction Temperature

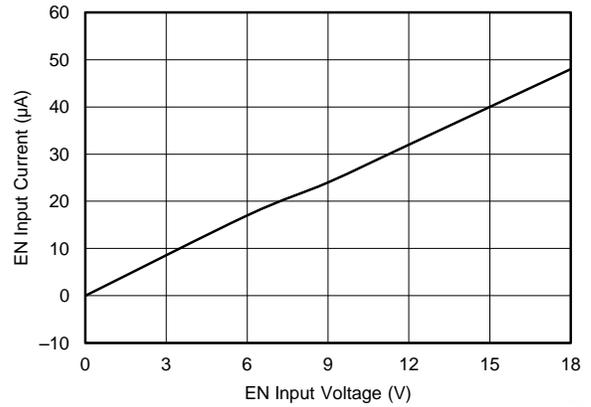


Figure 12. EN Current vs EN Voltage

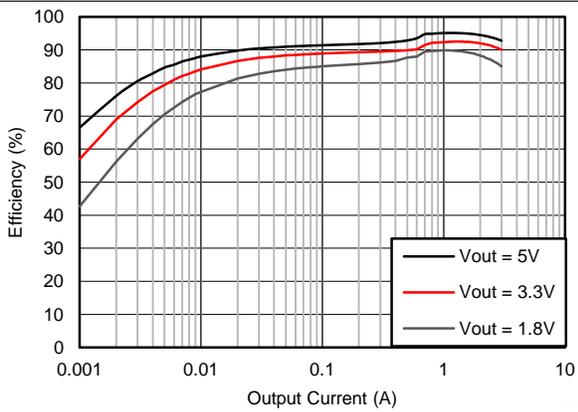


Figure 13. Efficiency vs Output Current

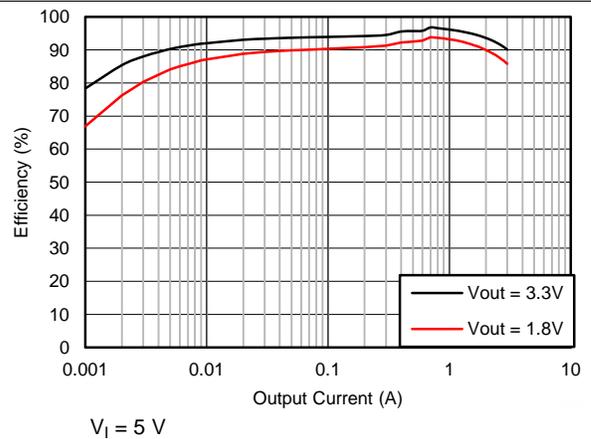
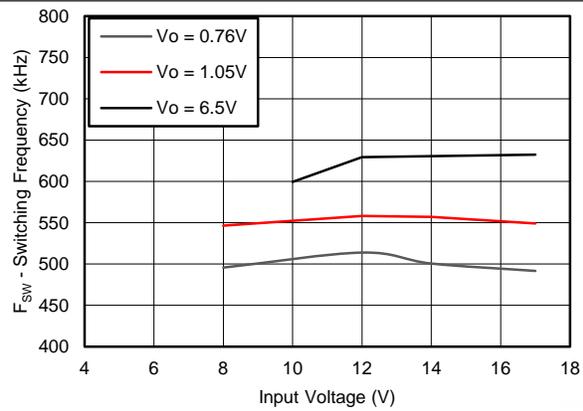
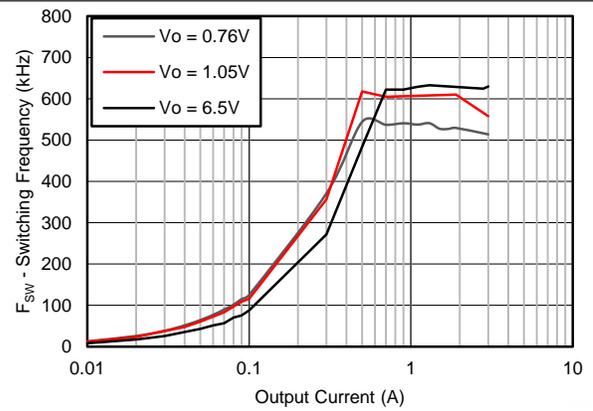


Figure 14. Efficiency vs Output Current

Typical Characteristics: TPS563210 (continued)
 $V_{IN} = 12V$ (unless otherwise noted)

Figure 15. Switching Frequency vs Input Voltage

Figure 16. Switching Frequency vs Output Current

Feature Description (continued)

At the beginning of each cycle, the high-side MOSFET is turned on. This MOSFET is turned off after internal one shot timer expires. This one shot duration is set proportional to the converter input voltage, V_{IN} , and inversely proportional to the output voltage, V_O , to maintain a pseudo-fixed frequency over the input voltage range, hence it is called adaptive on-time control. The one-shot timer is reset and the high-side MOSFET is turned on again when the feedback voltage falls below the reference voltage. An internal ramp is added to reference voltage to simulate output ripple, eliminating the need for ESR induced output ripple from D-CAP2™ mode control.

8.3.2 Soft Start and Pre-Biased Soft Start

The TPS562210 and TPS563210 have adjustable soft-start. When the EN pin becomes high, the SS charge current (I_{SS}) begins charging the capacitor which is connected from the SS pin to GND (C_{SS}). Smooth control of the output voltage is maintained during start up. The equation for the soft start time, T_{SS} is shown in Equation 1.

$$T_{SS}(\text{ms}) = \frac{C_{SS} \times V_{FBTH} \times 1.1}{I_{SS}} \quad (1)$$

where V_{FBTH} is 0.765V and I_{SS} is 6 μ A.

If the output capacitor is pre-biased at startup, the devices initiate switching and start ramping up only after the internal reference voltage becomes greater than the feedback voltage V_{FB} . This scheme ensures that the converters ramp up smoothly into regulation point.

8.3.3 Power Good

The power good output, PG is an open drain output. The power good function becomes active after 1.7 times soft-start time. When the output voltage becomes within –10% of the target value, internal comparators detect power good state and the power good signal becomes high. If the feedback voltage goes under 15% of the target value, the power good signal becomes low.

8.3.4 Current Protection

The output over-current limit (OCL) is implemented using a cycle-by-cycle valley detect control circuit. The switch current is monitored during the OFF state by measuring the low-side FET drain to source voltage. This voltage is proportional to the switch current. To improve accuracy, the voltage sensing is temperature compensated.

During the on time of the high-side FET switch, the switch current increases at a linear rate determined by V_{in} , V_{out} , the on-time and the output inductor value. During the on time of the low-side FET switch, this current decreases linearly. The average value of the switch current is the load current I_{out} . If the monitored current is above the OCL level, the converter maintains low-side FET on and delays the creation of a new set pulse, even the voltage feedback loop requires one, until the current level becomes OCL level or lower. In subsequent switching cycles, the on-time is set to a fixed value and the current is monitored in the same manner. If the over current condition exists consecutive switching cycles, the internal OCL threshold is set to a lower level, reducing the available output current. When a switching cycle occurs where the switch current is not above the lower OCL threshold, the counter is reset and the OCL threshold is returned to the higher value.

There are some important considerations for this type of over-current protection. The load current is higher than the over-current threshold by one half of the peak-to-peak inductor ripple current. Also, when the current is being limited, the output voltage tends to fall as the demanded load current may be higher than the current available from the converter. This may cause the output voltage to fall. When the VFB voltage falls below the UVP threshold voltage, the UVP comparator detects it. And then, the device will shut down after the UVP delay time (typically 14 μ s) and re-start after the hiccup time.

When the over current condition is removed, the output voltage returns to the regulated value.

8.3.5 Over Voltage Protection

TPS562210 and TPS563210 detect over voltage condition by monitoring the feedback voltage (VFB). When the feedback voltage becomes higher than 125% of the target voltage, the OVP comparator output goes high and the high-side MOSFET is turns off. This function is non-latch operation.

Feature Description (continued)

8.3.6 UVLO Protection

Under voltage lock out protection (UVLO) monitors the internal regulator voltage. When the voltage is lower than UVLO threshold voltage, the device is shut off. This protection is non-latching.

8.3.7 Thermal Shutdown

The device monitors the temperature of itself. If the temperature exceeds the threshold value (typically 155°C), the device is shut off. This is a non-latch protection.

8.4 Device Functional Modes

8.4.1 Advanced Eco-Mode™ Control

The TPS562210 and TPS563210 are designed with Advanced Eco-mode™ to maintain high light load efficiency. As the output current decreases from heavy load condition, the inductor current is also reduced and eventually comes to point that its rippled valley touches zero level, which is the boundary between continuous conduction and discontinuous conduction modes. The rectifying MOSFET is turned off when the zero inductor current is detected. As the load current further decreases the converter runs into discontinuous conduction mode. The on-time is kept almost the same as it was in the continuous conduction mode so that it takes longer time to discharge the output capacitor with smaller load current to the level of the reference voltage. This makes the switching frequency lower, proportional to the load current, and keeps the light load efficiency high. The transition point to the light load operation $I_{OUT(LL)}$ current can be calculated in [Equation 2](#).

$$I_{OUT(LL)} = \frac{1}{2 \times L \times f_{SW}} \times \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{V_{IN}} \quad (2)$$

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TPS562210 and TPS563210 are typically used as step down converters, which convert a voltage from 4.5 V to 17 V to a lower voltage. Webench software is available to aid in the design and analysis of circuits.

9.2 Typical Application

9.2.1 TPS562210 4.5-V to 17-V Input, 1.05-V output Converter

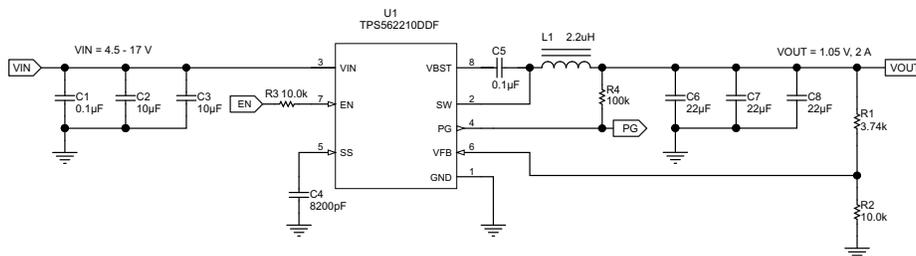


Figure 18. TPS562210 1.05V/2A Reference Design

9.2.1.1 Design Requirements

For this design example, use the parameters shown in [Table 1](#).

Table 1. Design Parameters

PARAMETER	VALUES
Input voltage range	4.5 V to 17 V
Output voltage	1.05 V
Output current	2 A
Output voltage ripple	20 mVp-p

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Output Voltage Resistors Selection

The output voltage is set with a resistor divider from the output node to the VFB pin. It is recommended to use 1% tolerance or better divider resistors. Start by using [Equation 3](#) to calculate V_{OUT} .

To improve efficiency at light loads consider using larger value resistors, too high of resistance are more susceptible to noise and voltage errors from the VFB input current are more noticeable.

$$V_{OUT} = 0.765 \times \left(1 + \frac{R1}{R2} \right) \quad (3)$$

9.2.1.2.2 Output Filter Selection

The LC filter used as the output filter has double pole at:

$$F_P = \frac{1}{2\pi\sqrt{L_{OUT} \times C_{OUT}}} \quad (4)$$

At low frequencies, the overall loop gain is set by the output set-point resistor divider network and the internal gain of the device. The low frequency phase is 180 degrees. At the output filter pole frequency, the gain rolls off at a –40 dB per decade rate and the phase drops rapidly. D-CAP2™ introduces a high frequency zero that reduces the gain roll off to –20 dB per decade and increases the phase to 90 degrees one decade above the zero frequency. The inductor and capacitor for the output filter must be selected so that the double pole of Equation 4 is located below the high frequency zero but close enough that the phase boost provided by the high frequency zero provides adequate phase margin for a stable circuit. To meet this requirement use the values recommended in Table 2.

Table 2. TPS562210 Recommended Component Values

Output Voltage (V)	R2 (kΩ)	R3 (kΩ)	L1 (μH)			C6 + C7 + C8 (μF)
			MIN	TYP	MAX	
1	3.09	10.0	1.5	2.2	4.7	20 - 68
1.05	3.74	10.0	1.5	2.2	4.7	20 - 68
1.2	5.76	10.0	1.5	2.2	4.7	20 - 68
1.5	9.53	10.0	1.5	2.2	4.7	20 - 68
1.8	13.7	10.0	1.5	2.2	4.7	20 - 68
2.5	22.6	10.0	2.2	3.3	4.7	20 - 68
3.3	33.2	10.0	2.2	3.3	4.7	20 - 68
5	54.9	10.0	3.3	4.7	4.7	20 - 68
6.5	75	10.0	3.3	4.7	4.7	20 - 68

The inductor peak-to-peak ripple current, peak current and RMS current are calculated using Equation 5, Equation 6 and Equation 7. The inductor saturation current rating must be greater than the calculated peak current and the RMS or heating current rating must be greater than the calculated RMS current.

Use 650 kHz for f_{SW} . Make sure the chosen inductor is rated for the peak current of Equation 6 and the RMS current of Equation 7.

$$I_{P-P} = \frac{V_{OUT}}{V_{IN(MAX)}} \times \frac{V_{IN(MAX)} - V_{OUT}}{L_O \times f_{SW}} \quad (5)$$

$$I_{PEAK} = I_O + \frac{I_{P-P}}{2} \quad (6)$$

$$I_{LO(RMS)} = \sqrt{I_O^2 + \frac{1}{12} I_{P-P}^2} \quad (7)$$

For this design example, the calculated peak current is 2.34 A and the calculated RMS current is 2.01 A. The inductor used is a TDK CLF7045T-2R2N with a peak current rating of 5.5 A and an RMS current rating of 4.3 A.

The capacitor value and ESR determines the amount of output voltage ripple. The TPS562210 and TPS563210 are intended for use with ceramic or other low ESR capacitors. Recommended values range from 20μF to 68μF. Use Equation 8 to determine the required RMS current rating for the output capacitor.

$$I_{CO(RMS)} = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{\sqrt{12} \times V_{IN} \times L_O \times f_{SW}} \quad (8)$$

For this design, two TDK C3216X5R0J226M 22 μF output capacitors are used. The typical ESR is 2 mΩ each. The calculated RMS current is 0.286A and each output capacitor is rated for 4A.

9.2.1.2.3 Input Capacitor Selection

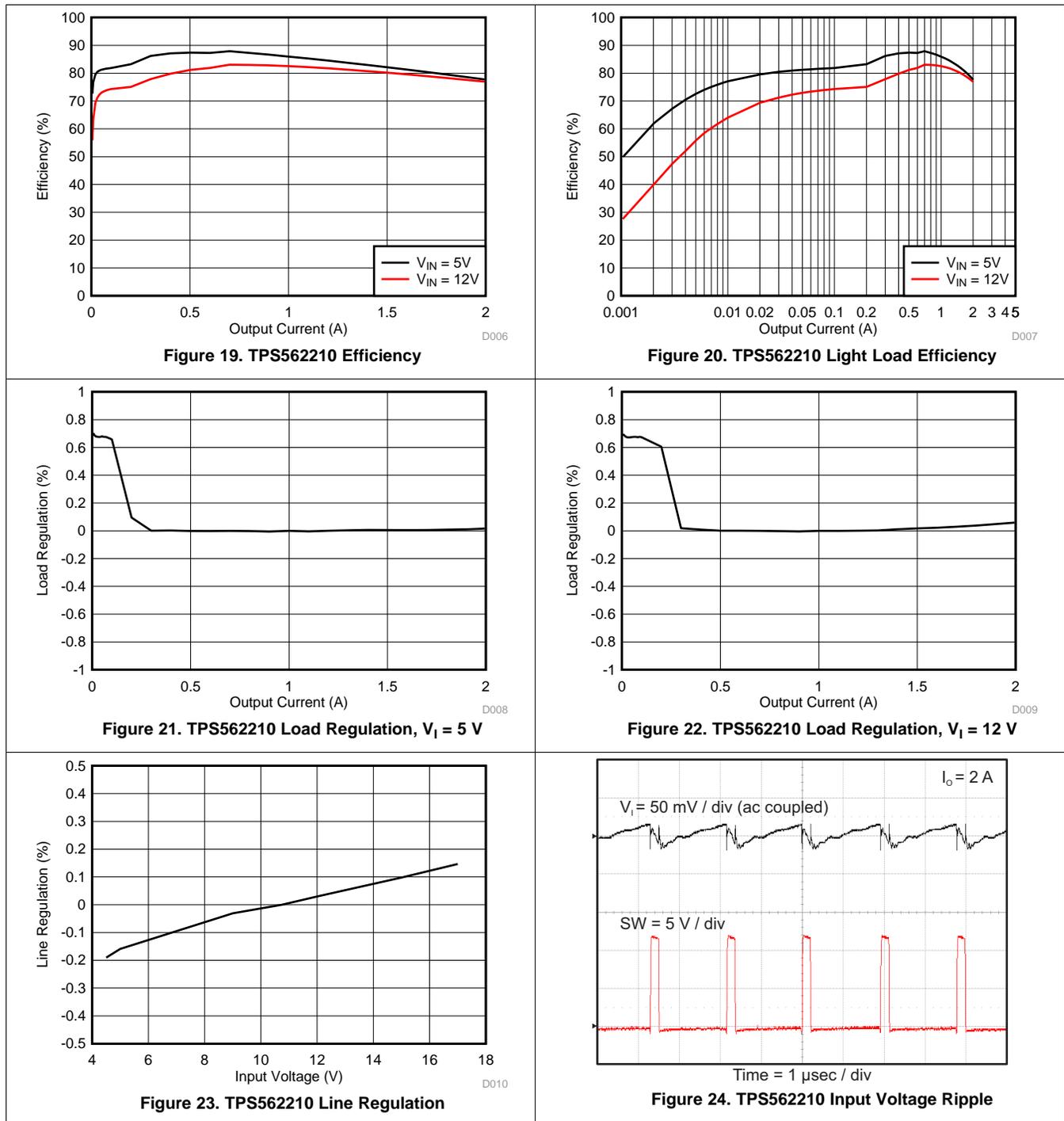
The TPS562210 and TPS563210 require an input decoupling capacitor and a bulk capacitor is needed depending on the application. A ceramic capacitor over 10 μF is recommended for the decoupling capacitor. An additional 0.1 μF capacitor (C3) from pin 3 to ground is optional to provide additional high frequency filtering. The capacitor voltage rating needs to be greater than the maximum input voltage.

9.2.1.2.4 Bootstrap capacitor Selection

A 0.1µF ceramic capacitor must be connected between the VBST to SW pin for proper operation. It is recommended to use a ceramic capacitor.

9.2.1.3 Application Curves

The following application curves were generated using the application circuit of Figure 18.



The following application curves were generated using the application circuit of Figure 18.

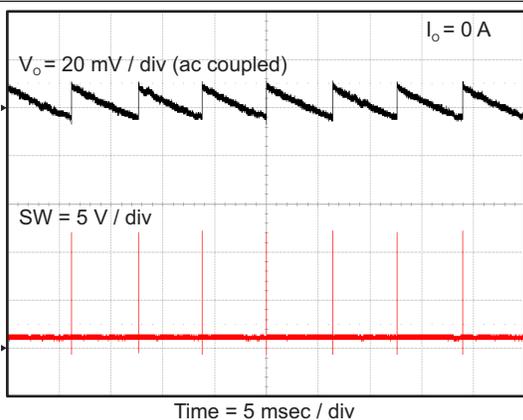


Figure 25. TPS562210 Output Voltage Ripple

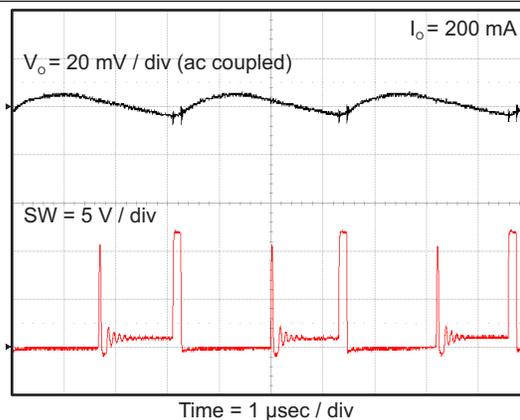


Figure 26. TPS562210 Output Voltage Ripple

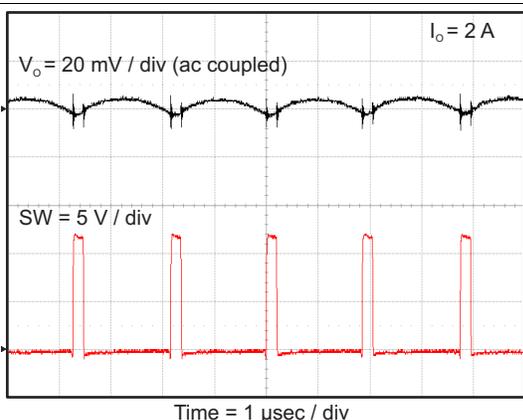


Figure 27. TPS562210 Output Voltage Ripple

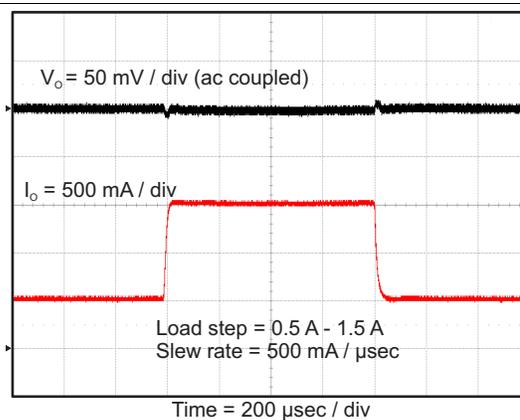


Figure 28. TPS562210 Transient Response

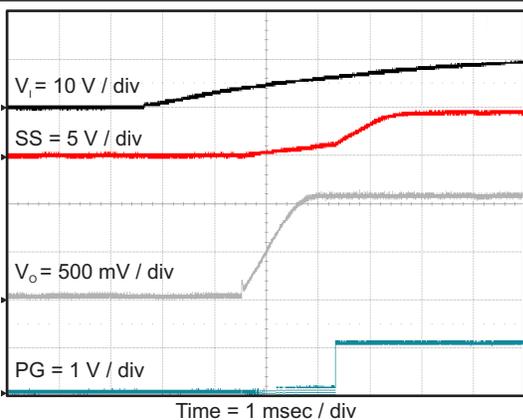


Figure 29. TPS562210 Start Up Relative To V_i

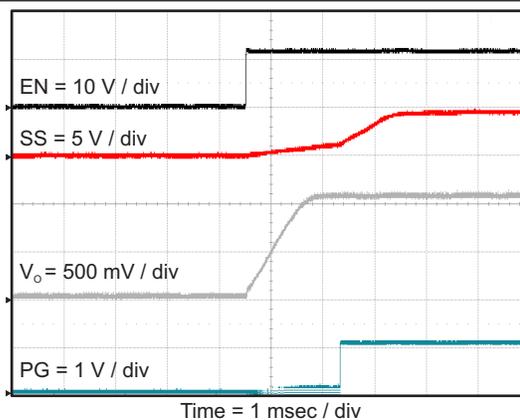


Figure 30. TPS562210 Start Up Relative To En

The following application curves were generated using the application circuit of [Figure 18](#).

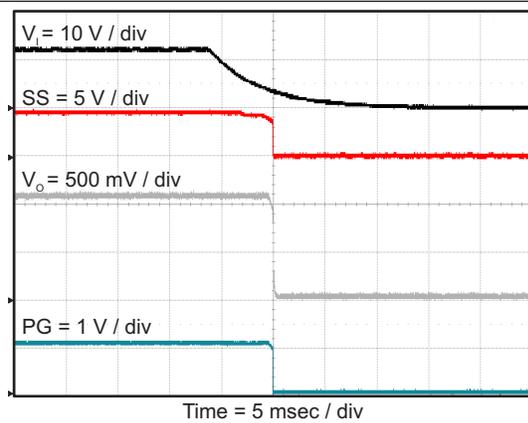


Figure 31. TPS562210 Shut Down Relative To V_i

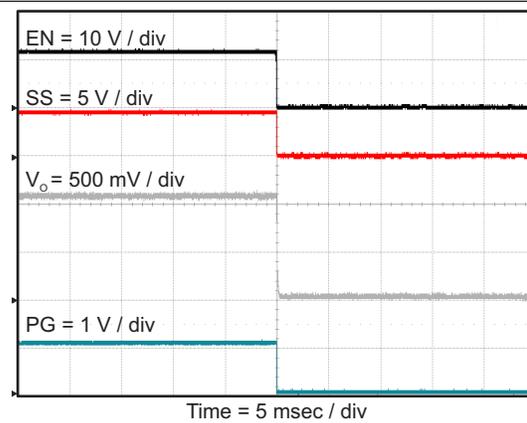


Figure 32. TPS562210 Shut Down Relative To EN

The following application curves were generated using the application circuit of Figure 18.

9.2.2 TPS563210 4.5-V To 17-V Input, 1.05-V Output Converter

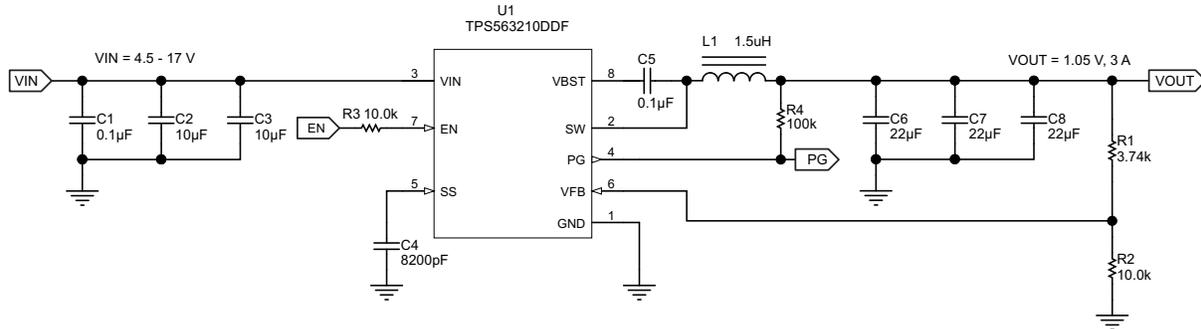


Figure 33. TPS563210 1.05 V / 3A Reference Design

9.2.2.1 Design Requirements

For this design example, use the parameters shown in Table 3.

Table 3. Design Parameters

PARAMETER	VALUE
Input voltage range	4.5 V to 17 V
Output voltage	1.05 V
Output current	3 A
Output voltage ripple	20 mVpp

9.2.2.2 Detailed Design Procedures

The detailed design procedure for TPS563210 is the same as for TPS562210 except for inductor selection.

9.2.2.2.1 Output Filter Selection

Table 4. TPS563210 Recommended Component Values

Output Voltage (V)	R2 (kΩ)	R3 (kΩ)	L1 (µH)			C6 + C7 + C8 (µF)
			MIN	TYP	MAX	
1	3.09	10.0	1.0	1.5	4.7	20 - 68
1.05	3.74	10.0	1.0	1.5	4.7	20 - 68
1.2	5.76	10.0	1.0	1.5	4.7	20 - 68
1.5	9.53	10.0	1.0	1.5	4.7	20 - 68
1.8	13.7	10.0	1.5	2.2	4.7	20 - 68
2.5	22.6	10.0	1.5	2.2	4.7	20 - 68
3.3	33.2	10.0	1.5	2.2	4.7	20 - 68
5	54.9	10.0	2.2	3.3	4.7	20 - 68
6.5	75	10.0	2.2	3.3	4.7	20 - 68

The inductor peak-to-peak ripple current, peak current and RMS current are calculated using Equation 9, Equation 10 and Equation 11. The inductor saturation current rating must be greater than the calculated peak current and the RMS or heating current rating must be greater than the calculated RMS current. Use 650 kHz for f_{sw} .

Use 650 kHz for f_{sw} . Make sure the chosen inductor is rated for the peak current of Equation 10 and the RMS current of Equation 11.

$$I_{P-P} = \frac{V_{OUT}}{V_{IN(MAX)}} \times \frac{V_{IN(MAX)} - V_{OUT}}{L_O \times f_{SW}} \tag{9}$$

$$I_{PEAK} = I_O + \frac{I_{P-P}}{2} \tag{10}$$

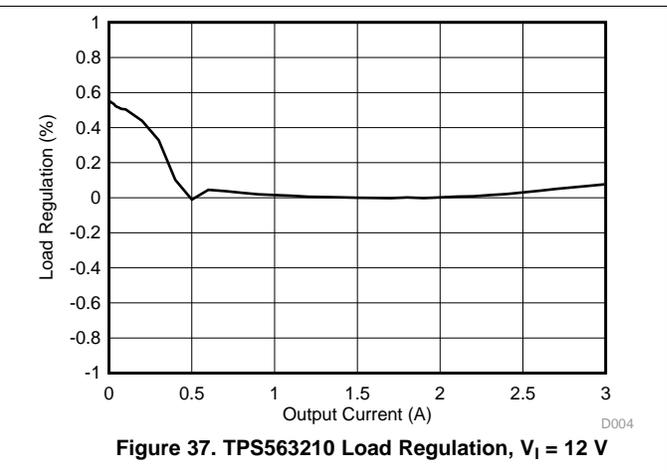
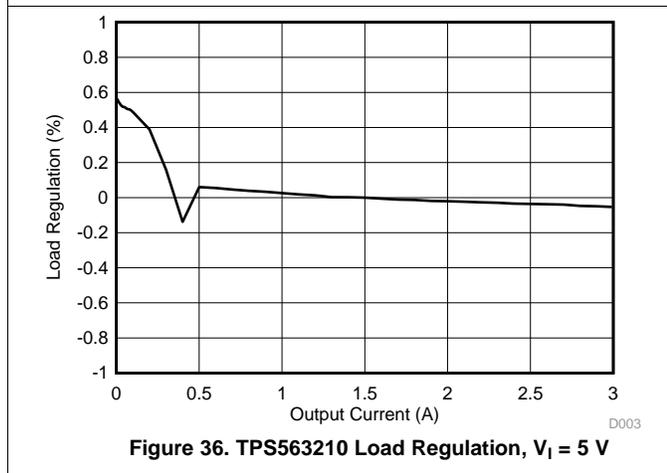
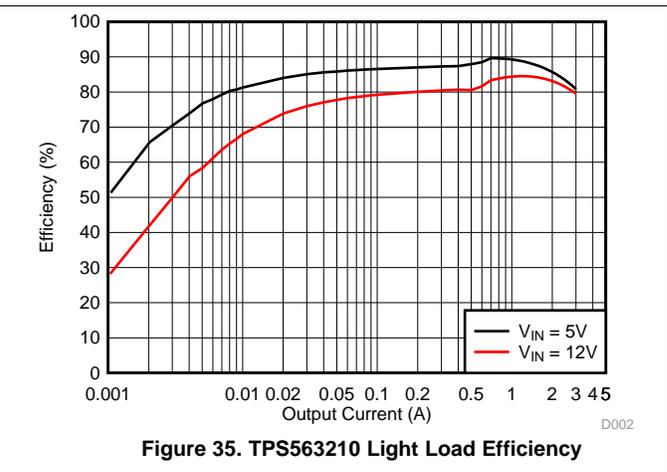
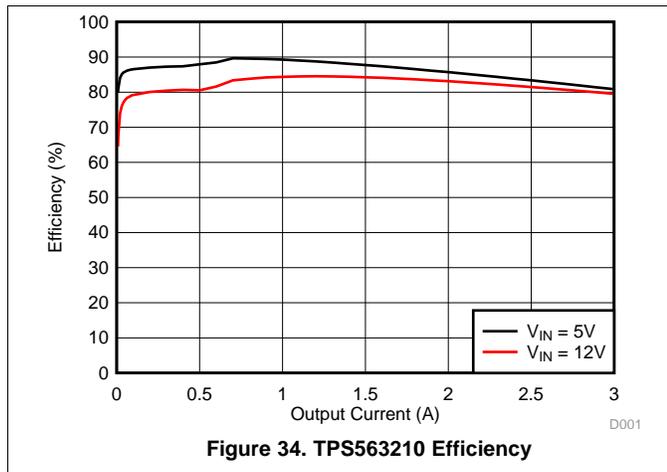
$$I_{LO(RMS)} = \sqrt{I_O^2 + \frac{1}{12} I_{P-P}^2} \tag{11}$$

For this design example, the calculated peak current is 3.505 A and the calculated RMS current is 3.014 A. The inductor used is a TDK CLF7045T-1R5N with a peak current rating of 7.3-A and an RMS current rating of 4.9-A.

The capacitor value and ESR determines the amount of output voltage ripple. The TPS563209 is intended for use with ceramic or other low ESR capacitors. Recommended values range from 20 μF to 68 μF. Use Equation 7 to determine the required RMS current rating for the output capacitor. For this design three TDK C3216X5R0J226M 22 μF output capacitors are used. The typical ESR is 2 mΩ each. The calculated RMS current is 0.292A and each output capacitor is rated for 4 A.

9.2.2.3 Application Curves

The following application curves were generated using the application circuit of Figure 33.



The following application curves were generated using the application circuit of Figure 33.

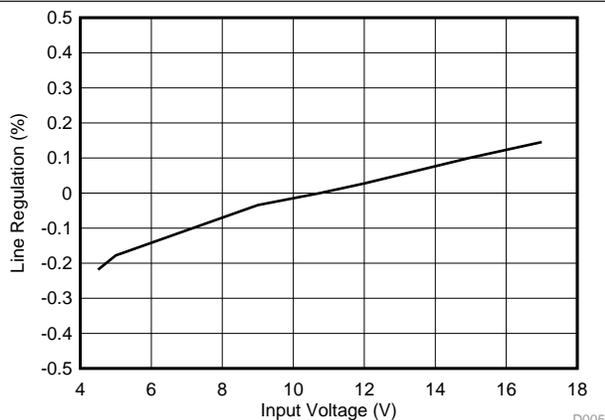


Figure 38. TPS563210 Line Regulation

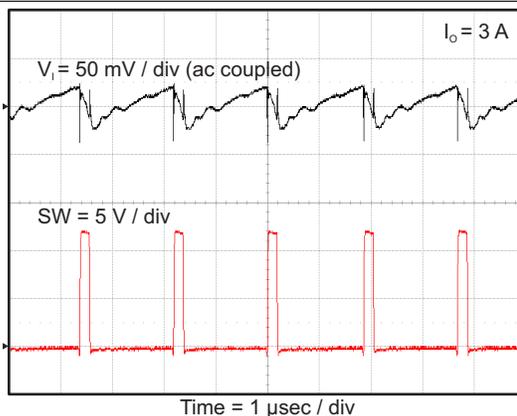


Figure 39. TPS563210 Input Voltage Ripple

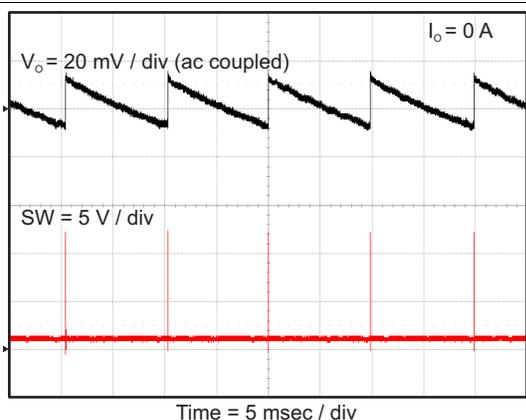


Figure 40. TPS563210 Output Voltage Ripple

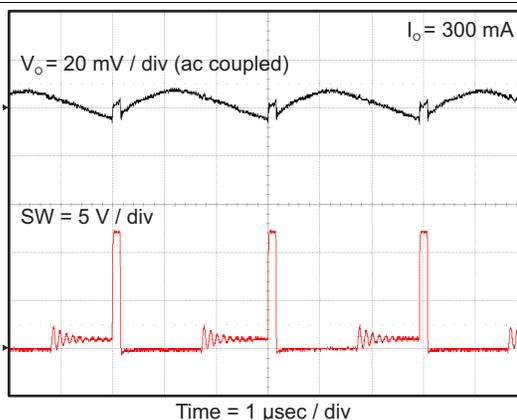


Figure 41. TPS563210 Output Voltage Ripple

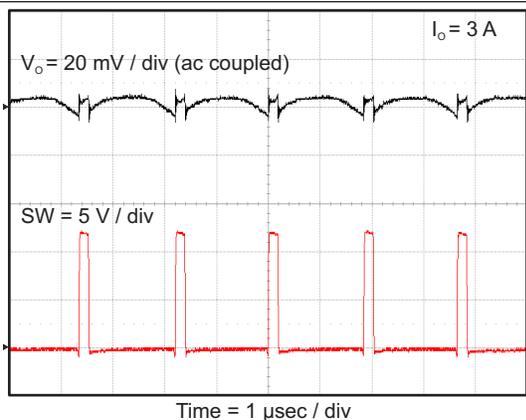


Figure 42. TPS563210 Output Voltage Ripple

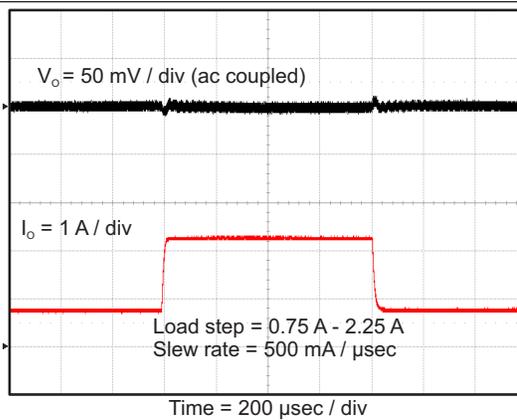


Figure 43. TPS563210 Transient Response

TPS562210, TPS563210

ZHCSE05A – FEBRUARY 2015 – REVISED AUGUST 2015

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The following application curves were generated using the application circuit of [Figure 33](#).

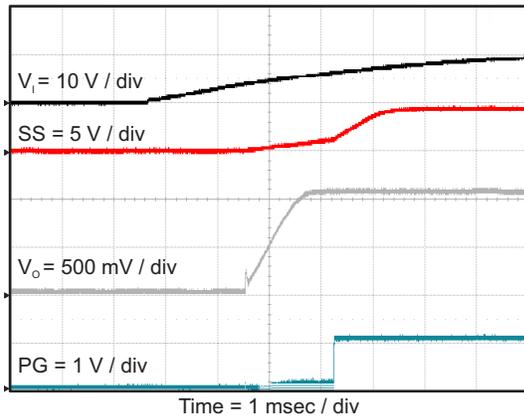


Figure 44. TPS563210 Start Up Relative To V_I

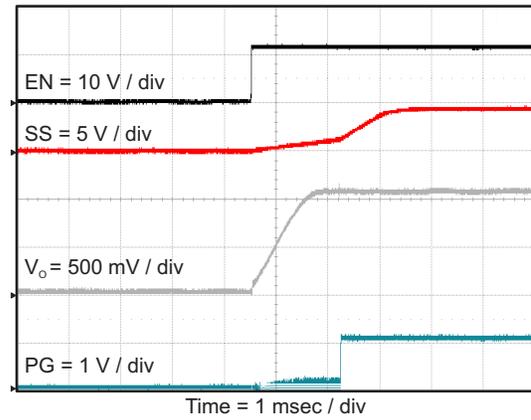


Figure 45. TPS563210 Start Up Relative To EN

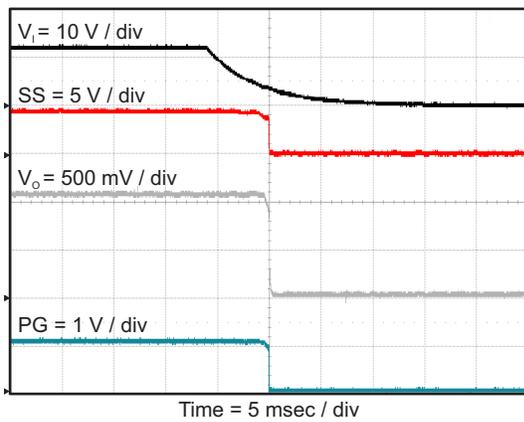


Figure 46. TPS563210 Shut Down Relative To V_I

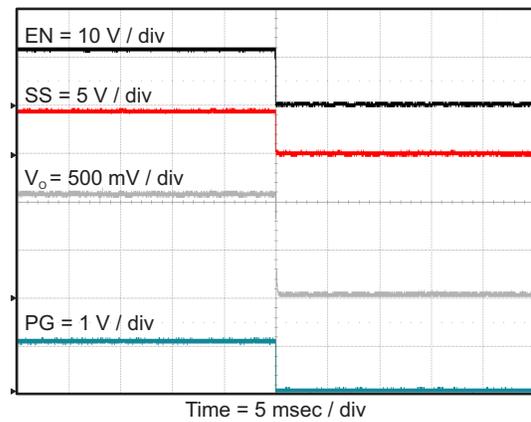


Figure 47. TPS563210 Shut Down Relative To EN

10 Power Supply Recommendations

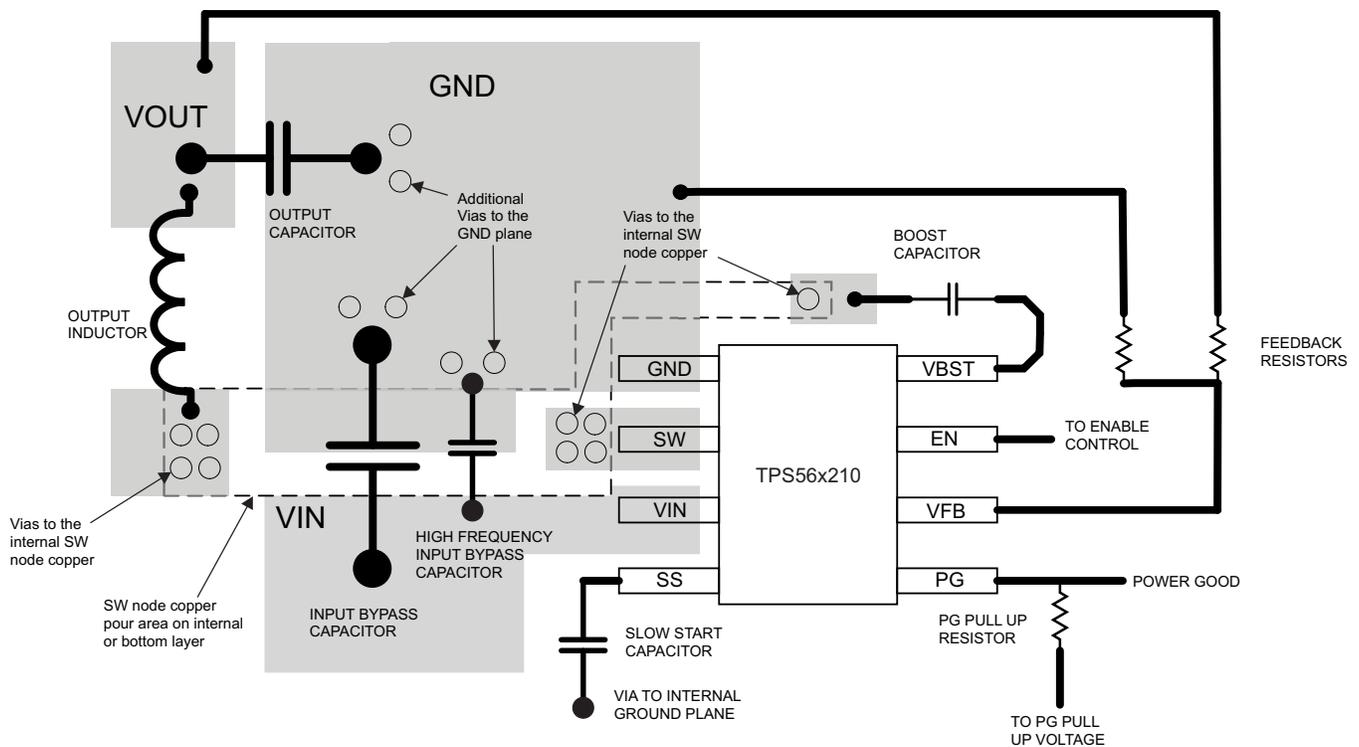
The TPS562210 and TPS563210 are designed to operate from input supply voltage in the range of 4.5 V to 17 V. Buck converters require the input voltage to be higher than the output voltage for proper operation. The maximum recommended operating duty cycle is 65%. Using that criteria, the minimum recommended input voltage is $V_O / 0.65$.

11 Layout

11.1 Layout Guidelines

1. VIN and GND traces should be as wide as possible to reduce trace impedance. The wide areas are also of advantage from the view point of heat dissipation.
2. The input capacitor and output capacitor should be placed as close to the device as possible to minimize trace impedance.
3. Provide sufficient vias for the input capacitor and output capacitor.
4. Keep the SW trace as physically short and wide as practical to minimize radiated emissions.
5. Do not allow switching current to flow under the device.
6. A separate VOUT path should be connected to the upper feedback resistor.
7. Make a Kelvin connection to the GND pin for the feedback path.
8. Voltage feedback loop should be placed away from the high-voltage switching trace, and preferably has ground shield.
9. The trace of the VFB node should be as small as possible to avoid noise coupling.
10. The GND trace between the output capacitor and the GND pin should be as wide as possible to minimize its trace impedance.

11.2 Layout Example



12 器件和文档支持

12.1 相关链接

以下表格列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，并且可以快速访问样片或购买链接。

表 5. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
TPS562210	请单击此处				
TPS563210	请单击此处				

12.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 商标

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Blu-ray Disc is a trademark of Blu-ray Disc Association.

12.4 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS562210DDFR.A	NRND	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2210
TPS562210DDFR.B	NRND	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2210
TPS562210DDFT.A	NRND	Production	SOT-23-THIN (DDF) 8	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2210
TPS562210DDFT.B	NRND	Production	SOT-23-THIN (DDF) 8	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2210
TPS563210DDFR.A	NRND	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	3210
TPS563210DDFR.B	NRND	Production	SOT-23-THIN (DDF) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	3210
TPS563210DDFT.A	NRND	Production	SOT-23-THIN (DDF) 8	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	3210
TPS563210DDFT.B	NRND	Production	SOT-23-THIN (DDF) 8	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	3210

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

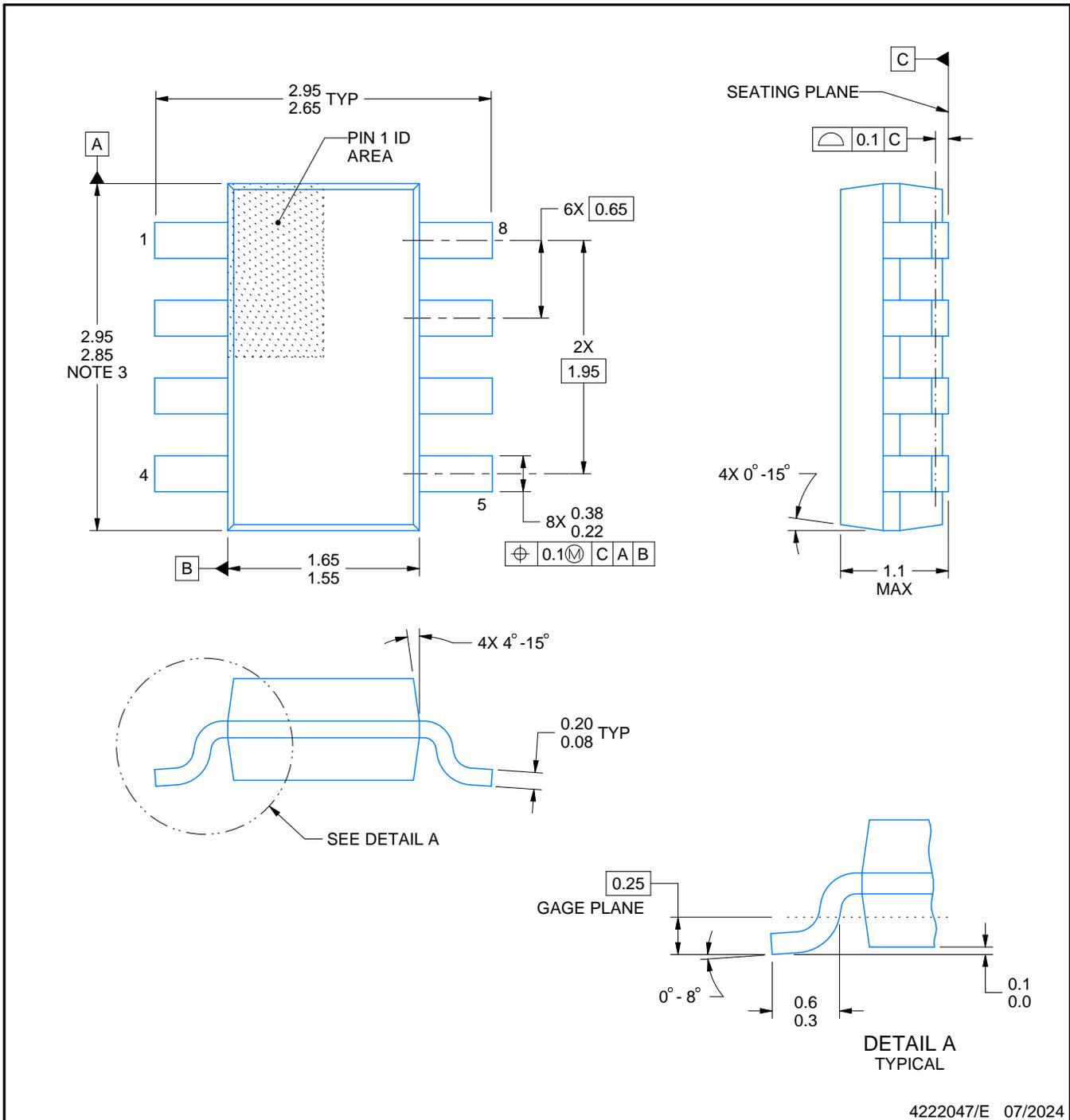
DDF0008A



PACKAGE OUTLINE

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



4222047/E 07/2024

NOTES:

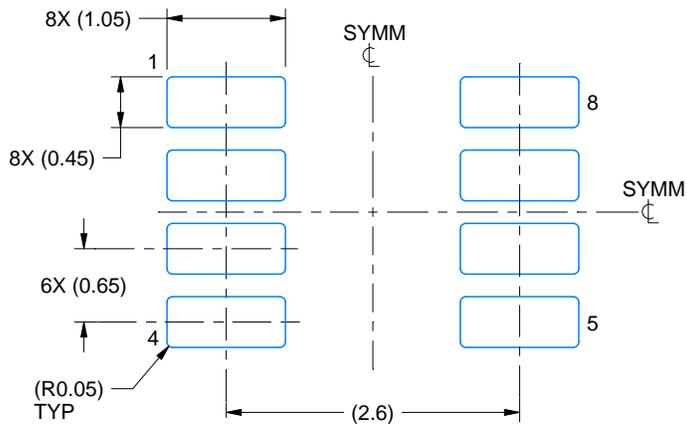
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

EXAMPLE BOARD LAYOUT

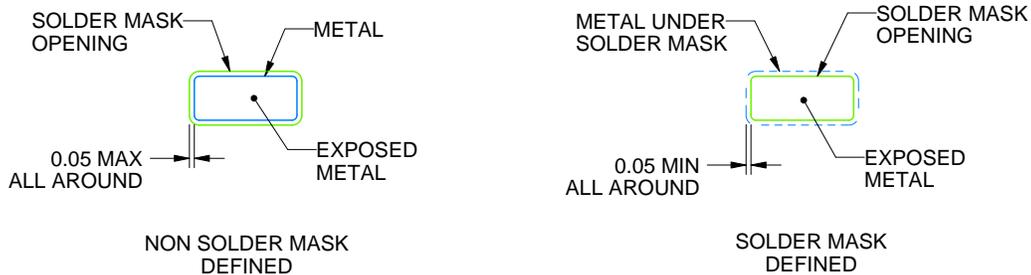
DDF0008A

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

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NOTES: (continued)

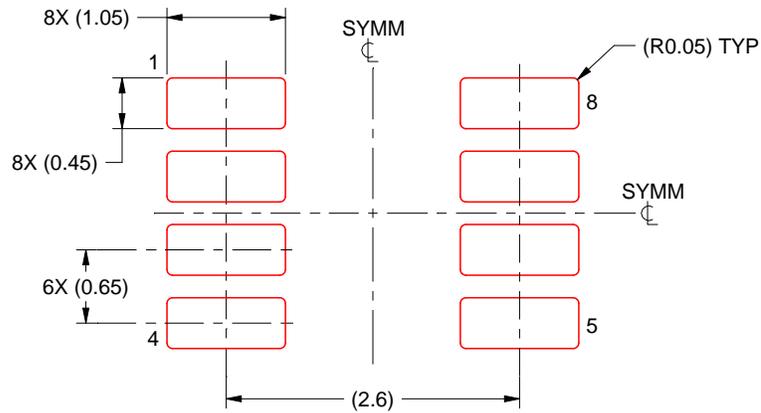
- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DDF0008A

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4222047/E 07/2024

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

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